

CORRECTION

[View Article Online](#)
[View Journal](#) | [View Issue](#)



Cite this: *J. Mater. Chem. C*, 2021, **9**, 17542

Correction: Epitaxial growth of β -Ga₂O₃ (–201) thin film on four-fold symmetry CeO₂ (001) substrate for heterogeneous integrations

Xiao Tang,^{*a} Kuang-Hui Li,^a Che-Hao Liao,^a Dongxing Zheng,^b Chen Liu,^b Rongyu Lin,^a Na Xiao,^a Shibin Krishna,^a Jose Tauboda^a and Xiaohang Li^{*a}

DOI: 10.1039/d1tc90261j

rsc.li/materials-c

Correction for 'Epitaxial growth of β -Ga₂O₃ (–201) thin film on four-fold symmetry CeO₂ (001) substrate for heterogeneous integrations' by Xiao Tang *et al.*, *J. Mater. Chem. C*, 2021, **9**, 15868–15876, DOI: 10.1039/D1TC02852A.

The authors regret the omission of the email address for the co-corresponding author, Xiaohang Li, from the original published article. Their email address is Xiaohang.li@kaust.edu.sa, and the corrected author affiliation details are shown here.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

^a Advanced Semiconductor Laboratory, King Abdullah University of Science and Technology (KAUST), Thuwal 23955-6900, Saudi Arabia. E-mail: xiao.tang@kaust.edu.sa, Xiaohang.li@kaust.edu.sa

^b Division of Physical Science and Engineering (PSE), King Abdullah University of Science and Technology (KAUST), Thuwal 23955-6900, Saudi Arabia

